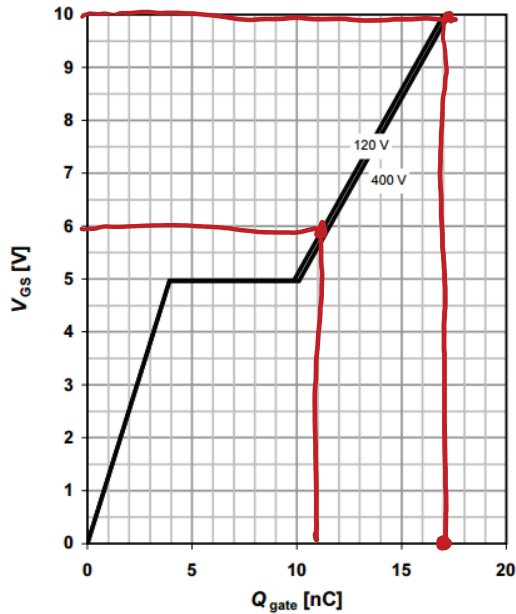


Gate Charge

9 Typ. gate charge

$V_{GS}=f(Q_{gate}); I_D=5.2 \text{ A pulsed}$

parameter: V_{DD}



Power supply
voltage of gate
driver

$$P_g = V_{GS} Q_g f_s$$

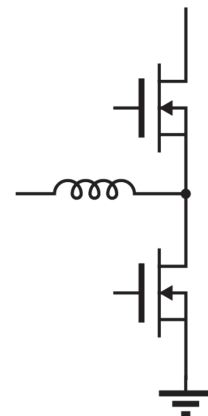
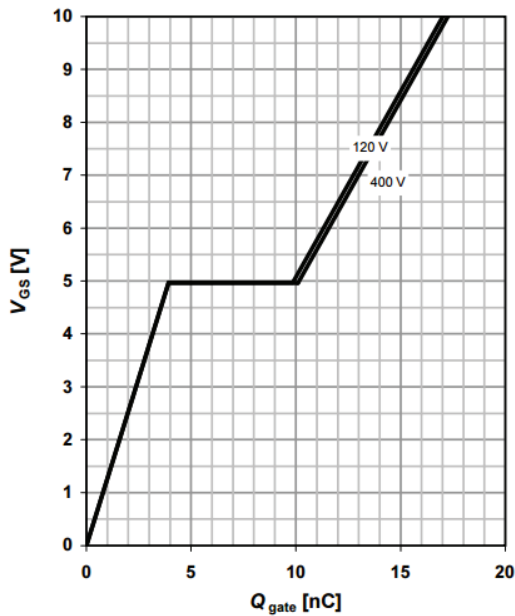
Overlap Time

9 Typ. gate charge

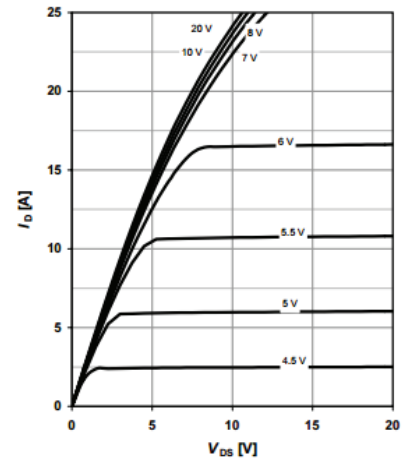
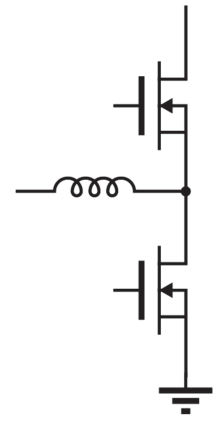
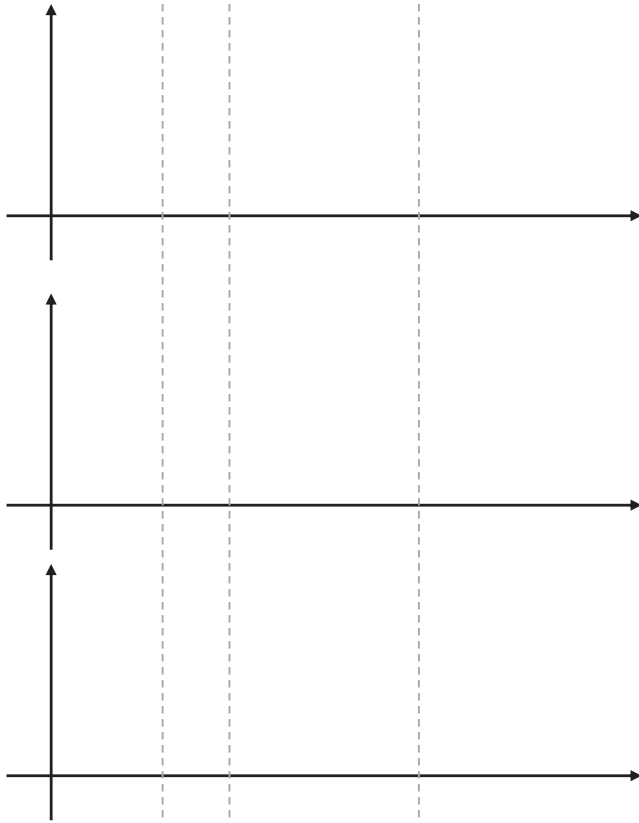
$V_{GS}=f(Q_{gate}); I_D=5.2 \text{ A pulsed}$

parameter: V_{DD}

Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=0.34 \text{ mA}$	2.5	3	3.5
Gate resistance	R_G	$f=1 \text{ MHz, open drain}$	-	1.8	-



FET Turn-On



Device Transconductance

